

09/03/01  
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ISSUE CLASSIFICATION	
Class	Subclass

**PATENT NUMBER**

## U.S. UTILITY Patent Application

<b>O.I.P.E.</b> mH SCANNED TR3 o.a. Ed	<b>PATENT DATE</b>
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APPLICATION NO. 09/924318	CONT/PRIOR	CLASS 438	SUBCLASS	ART UNIT 1765	EXAMINER Tran, B
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## APPLICANTS

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Jack Mandelberg


**TITLE**

Method of building a CMOS structure on thin Si with source/drain electrodes formed by in situ doped selective amorphous silicon

PTO-2040  
12/09

<b>ISSUING CLASSIFICATION</b>									
<b>ORIGINAL</b>			<b>CROSS REFERENCE(S)</b>						
<b>CLASS</b>	<b>SUBCLASS</b>	<b>CLASS</b>	<b>SUBCLASS (ONE SUBCLASS PER BLOCK)</b>						
<b>INTERNATIONAL CLASSIFICATION</b>									

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 <b>TERMINAL DISCLAIMER</b>	<b>DRAWINGS</b>		<b>CLAIMS ALLOWED</b>	
	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims
<input type="checkbox"/> The term of this patent subsequent to _____ (date) has been disclaimed.	_____ (Assistant Examiner) (Date)		<b>NOTICE OF ALLOWANCE MAILED</b>	
<input type="checkbox"/> The term of this patent shall not extend beyond the expiration date of U.S. Patent. No. _____ _____ _____	_____ (Primary Examiner) (Date)		<b>ISSUE FEE</b>	
			Amount Due	Date Paid
<input type="checkbox"/> The terminal _____ months of this patent have been disclaimed.	_____ (Legal Instruments Examiner) (Date)		<b>ISSUE BATCH NUMBER</b>	

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